

**PATENT APPLICATION**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of

Docket No: Q75721

Koichi TERASHIMA

Appln. No.: Unknown

Confirmation No.: Unknown

Group Art Unit: Unknown

Filed: August 21, 2003

Examiner: Unknown

For: SEMICONDUCTOR DEVICE AND SEMICONDUCTOR DEVICE  
MANUFACTURING METHOD

**INFORMATION DISCLOSURE STATEMENT  
UNDER 37 C.F.R. §§ 1.97 and 1.98**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant hereby notifies the U.S. Patent and Trademark Office of the documents which are listed on the attached PTO/SB/08 A & B (modified) form and/or listed herein and which the Examiner may deem material to patentability of the claims of the above-identified application.

1. JP-A 2001-267413 published September 28, 2001.
2. JP-A 2002-110780 published April 12, 2002.
3. T. MIZUNO et al., "Advanced SOI p-MOSFETs with Strained-Si Channel on SiGe-on-Insulator Substrate Fabricated by SIMOX Technology," *IEEE Transactions on Electron Devices*, Vol. 48, No. 8, August 2001, pp. 1612-1618.
4. JP-A 2994227 published October 22, 1999.
5. JP-B2 3221901 published August 17, 2001.

One copy of each of the listed documents is submitted herewith.


K. TERASHIMA  
Q75721  
Information Disclosure Statement

The present Information Disclosure Statement is being filed: (1) No later than three months from the application's filing date for an application other than a continued prosecution application (CPA) under §1.53(d); (2) Before the mailing date of the first Office Action on the merits (whichever is later); or (3) Before the mailing date of the first Office Action after filing a request for continued examination (RCE) under §1.114, and therefore, no Statement under 37 C.F.R. § 1.97(e) or fee under 37 C.F.R. § 1.17(p) is required.

In compliance with the concise explanation requirement under 37 C.F.R. § 1.98(a)(3) for foreign language documents, Applicant states that the references are discussed within the specification beginning at page 2, paragraphs 4-6.

The submission of the listed documents is not intended as an admission that any such document constitutes prior art against the claims of the present application. Applicant does not waive any right to take any action that would be appropriate to antedate or otherwise remove any listed document as a competent reference against the claims of the present application.

Respectfully submitted,

  
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WASHINGTON OFFICE  
**23373**  
CUSTOMER NUMBER

Date: August 21, 2003

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation*
		T. MIZUNO et al., "Advanced SOI p-MOSFETs with Strained-Si Channel on SiGe-on-Insulator Substrate Fabricated by SIMOX Technology," <i>IEEE Transactions on Electron Devices</i> , Vol. 48, No. 8, August 2001, pp. 1612-1618	

Examiner Signature		Date Considered	
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<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kind Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov), MPEP 901.04 or in the comment box of this document. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to indicate here if English language translation is attached.